2SB0950, 2SB0950A (2SB950, 2SB950A)

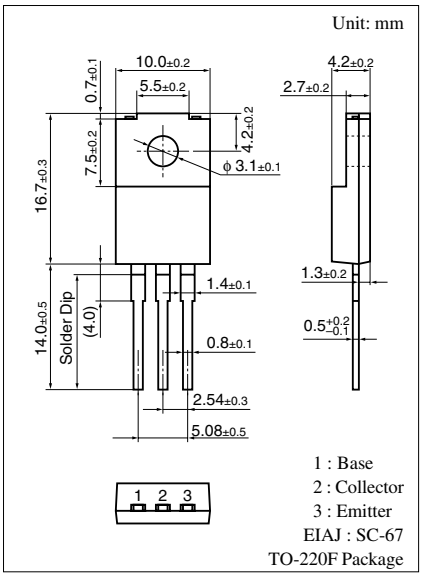
Silicon PNP epitaxial planar type Darlington

For power amplification and switching

Complementary to 2SD1276 and 2SD1276A

■ Features

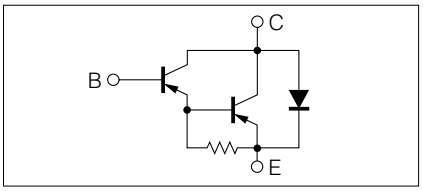
- High forward current transfer ratio h_{FE}
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw



■ Absolute Maximum Ratings $T_C = 25°C$

Parameter		Symbol	Rating	Unit
Collector to base voltage	2SB0950	V_{CBO}	−60	V
	2SB0950A		−80	
Collector to emitter voltage	2SB0950	V_{CEO}	−60	V
	2SB0950A		−80	
Emitter to base voltage		V_{EBO}	−5	V
Peak collector current		I_{CP}	−8	A
Collector current		I_C	−4	A
Collector power dissipation	$T_C = 25°C$	P_C	40	W
	$T_a = 25°C$		2	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	−55 to +150	°C

Internal Connection



■ Electrical Characteristics $T_C = 25°C$

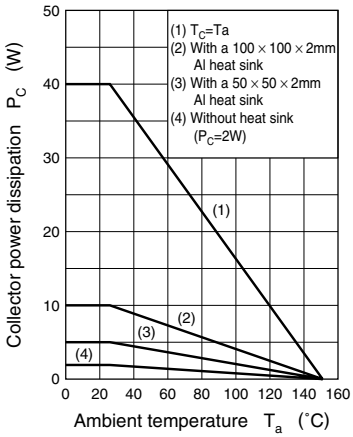
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	2SB0950	I_{CBO}	V_{CB} = −60 V, I_E = 0			−200	μA
	2SB0950A		V_{CB} = −80 V, I_E = 0			−200	
Collector cutoff current	2SB0950	I_{CEO}	V_{CE} = −30 V, I_B = 0			−500	μA
	2SB0950A		V_{CE} = −40 V, I_B = 0			−500	
Emitter cutoff current		I_{EBO}	V_{EB} = −5 V, I_C = 0			−2	mA
Collector to emitter voltage	2SB0950	V_{CEO}	I_C = −30 mA, I_B = 0	−60			V
	2SB0950A			−80			
Forward current transfer ratio		h_{FE1}	V_{CE} = −3 V, I_C = − 0.5 A	1 000			
		h_{FE2} *	V_{CE} = −3 V, I_C = −3 A	2 000		10 000	
Base to emitter voltage		V_{BE}	V_{CE} = −3 V, I_C = −3 A			−2.5	V
Collector to emitter saturation voltage		$V_{CE(sat)1}$	I_C = −3 A, I_B = −12 mA			−2	V
		$V_{CE(sat)2}$	I_C = −5 A, I_B = −20 mA			−4	V
Transition frequency		f_T	V_{CE} = −10 V, I_C = − 0.5 A, f = 1 MHz		20		MHz
Turn-on time		t_{on}	I_C = −3 A, I_{B1} = −12 mA, I_{B2} = 12 mA, V_{CC} = −50 V		0.3		μs
Storage time		t_{stg}			2		μs
Fall time		t_f			0.5		μs

Note) *: Rank classification

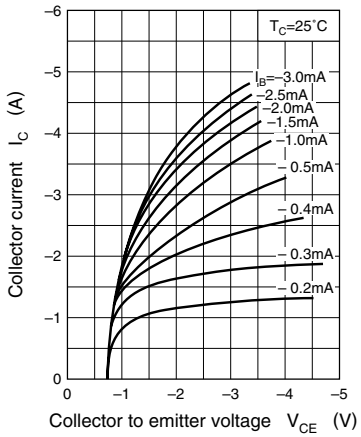
Rank	Q	P
h_{FE2}	2 000 to 5 000	4 000 to 10 000

Note.) The Part numbers in the Parenthesis show conventional part number.

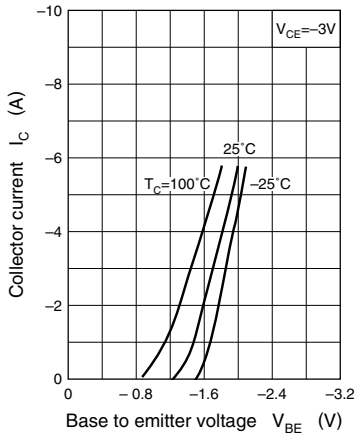
P_C — T_a



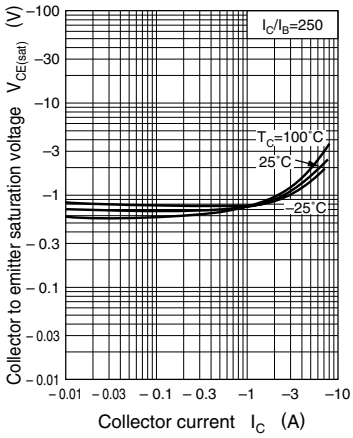
I_C — V_{CE}



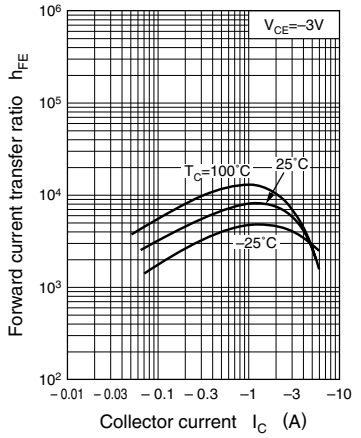
I_C — V_{BE}



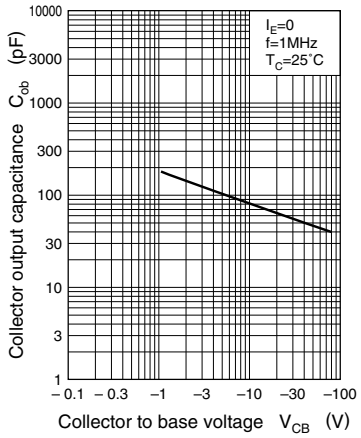
$V_{CE(sat)}$ — I_C



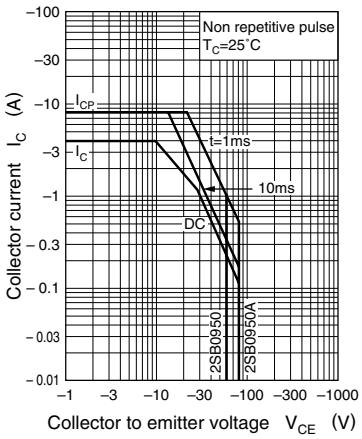
h_{FE} — I_C



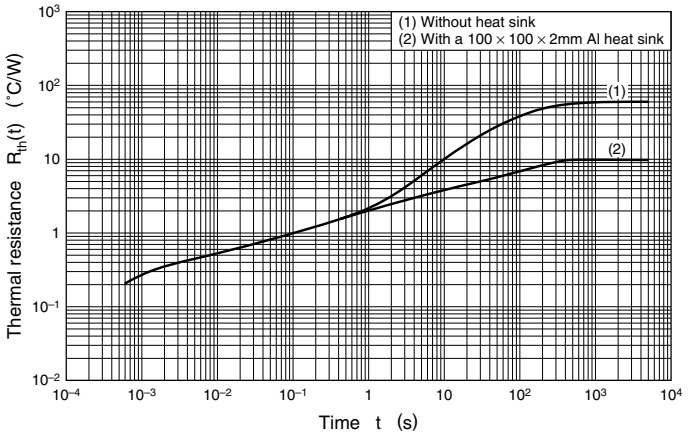
C_{ob} — V_{CB}



Area of safe operation (ASO)



$R_{th(t)}$ — t



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